

DATA SHEET



SILICON POWER MOS FET NE552R479A

3.0 V OPERATION SILICON RF POWER LDMOS FET FOR 2.45 GHz 0.4 W TRANSMISSION AMPLIFIERS

DESCRIPTION

The NE552R479A is an N-channel silicon power laterally diffused MOS FET specially designed as the transmission power amplifier for 3.0 V WLL products. Dies are manufactured using our NEWMOS2 technology (our WSi gate laterally diffused MOS FET) and housed in a surface mount package. This device can deliver 26.0 dBm output power with 45% power added efficiency at 2.45 GHz under the 3.0 V supply voltage.

FEATURES

- High output power : $P_{out} = 26.0$ dBm TYP. ($V_{DS} = 3.0$ V, $I_{Dset} = 200$ mA, $f = 2.45$ GHz, $P_{in} = 19$ dBm)
- High power added efficiency : $\eta_{add} = 45\%$ TYP. ($V_{DS} = 3.0$ V, $I_{Dset} = 200$ mA, $f = 2.45$ GHz, $P_{in} = 19$ dBm)
- High linear gain : $G_L = 11$ dB TYP. ($V_{DS} = 3.0$ V, $I_{Dset} = 200$ mA, $f = 2.45$ GHz, $P_{in} = 10$ dBm)
- Surface mount package : $5.7 \times 5.7 \times 1.1$ mm MAX.
- Single supply : $V_{DS} = 2.8$ to 6.0 V

APPLICATIONS

- Digital cellular phones : 3.0 V GSM1900 Pre Driver
- Analog cellular phones : 2.8 V AMPS Handsets
- Bluetooth™ applications : 3.0 V Class 1 Devices
- Others : 3.0 V Two-Way Pagers

ORDERING INFORMATION

Part Number	Package	Marking	Supplying Form
NE552R479A-T1	79A	AW	• 12 mm wide embossed taping • Gate pin face the perforation side of the tape • Qty 1 kpcs/reel
NE552R479A-T1A			• 12 mm wide embossed taping • Gate pin face the perforation side of the tape • Qty 5 kpcs/reel

Remark To order evaluation samples, contact your nearby sales office.

Part number for sample order: NE552R479A-A

Caution: Observe precautions when handling because these devices are sensitive to electrostatic discharge

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

ABSOLUTE MAXIMUM RATINGS ($T_A = +25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Drain to Source Voltage	V_{DS}	15.0	V
Gate to Source Voltage	V_{GS}	5.0	V
Drain Current	I_D	300	mA
Drain Current (Pulse Test)	I_D^{Note}	600	mA
Total Power Dissipation	P_{tot}	10	W
Channel Temperature	T_{ch}	125	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

Note Duty Cycle 50%, $T_{on} \leq 1 \text{ s}$

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	V_{DS}		2.8	3.0	6.0	V
Gate to Source Voltage	V_{GS}		0	2.0	3.0	V
Drain Current	I_D	Duty Cycle 50%, $T_{on} \leq 1 \text{ s}$	–	200	500	mA
Input Power	P_{in}	$f = 2.45 \text{ GHz}$, $V_{DS} = 3.0 \text{ V}$	18	19	25	dBm

ELECTRICAL CHARACTERISTICS

($T_A = +25^\circ\text{C}$, unless otherwise specified, using NEC standard test fixture)

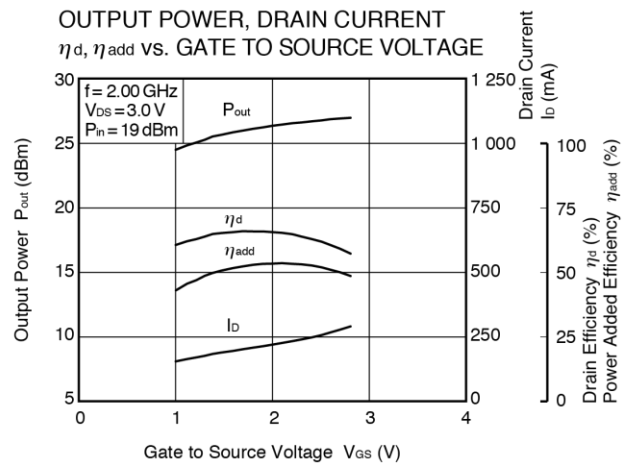
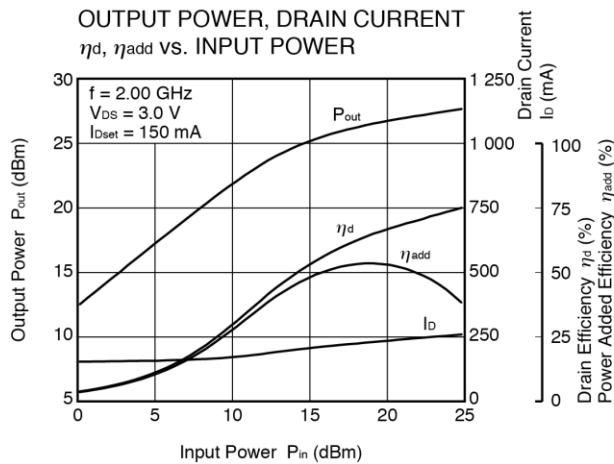
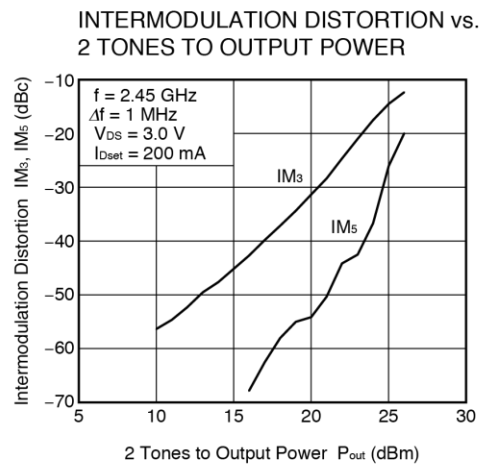
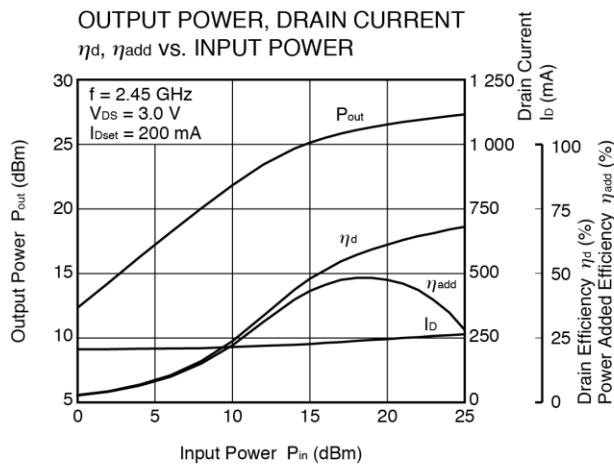
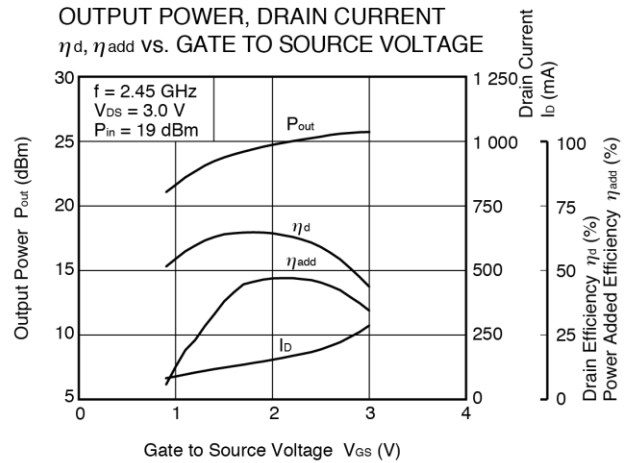
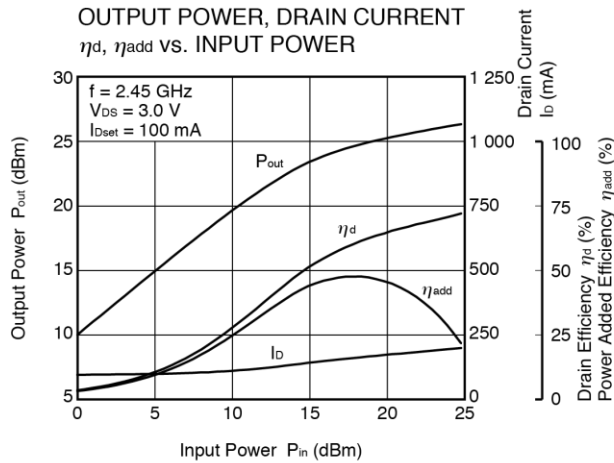
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Gate to Source Leak Current	I_{GSS}	$V_{GS} = 5.0 \text{ V}$	–	–	100	nA
Drain to Source Leakage Current (Zero Gate Voltage Drain Current)	I_{DSS}	$V_{DS} = 6.0 \text{ V}$	–	–	100	nA
Gate Threshold Voltage	V_{th}	$V_{DS} = 3.5 \text{ V}$, $I_D = 1 \text{ mA}$	1.0	1.4	1.9	V
Thermal Resistance	R_{th}	Channel to Case	–	–	10	$^\circ\text{C/W}$
Transconductance	G_m	$V_{DS} = 3.5 \text{ V}$, $I_D = 100 \text{ mA}$	–	0.4	–	S
Drain to Source Breakdown Voltage	BV_{DSS}	$I_{DSS} = 10 \mu\text{A}$	15	18	–	V
Output Power	P_{out}	$f = 2.45 \text{ GHz}$, $V_{DS} = 3.0 \text{ V}$, $P_{in} = 19 \text{ dBm}$, $I_{Dset} = 200 \text{ mA}$ (RF OFF), Note1	24.0	26.0	–	dBm
Drain Current	I_D		–	230	–	mA
Power Added Efficiency	η_{add}		35	45	–	%
Linear Gain ^{Note2}	G_L		–	11	–	dB

Notes 1. DC performance is 100% testing. RF performance is testing several samples per wafer.

Wafer rejection criteria for standard devices is 1 reject for several samples.

2. $P_{in} = 10 \text{ dBm}$

TYPICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$)



Remark The graphs indicate nominal characteristics.

S-PARAMETERS

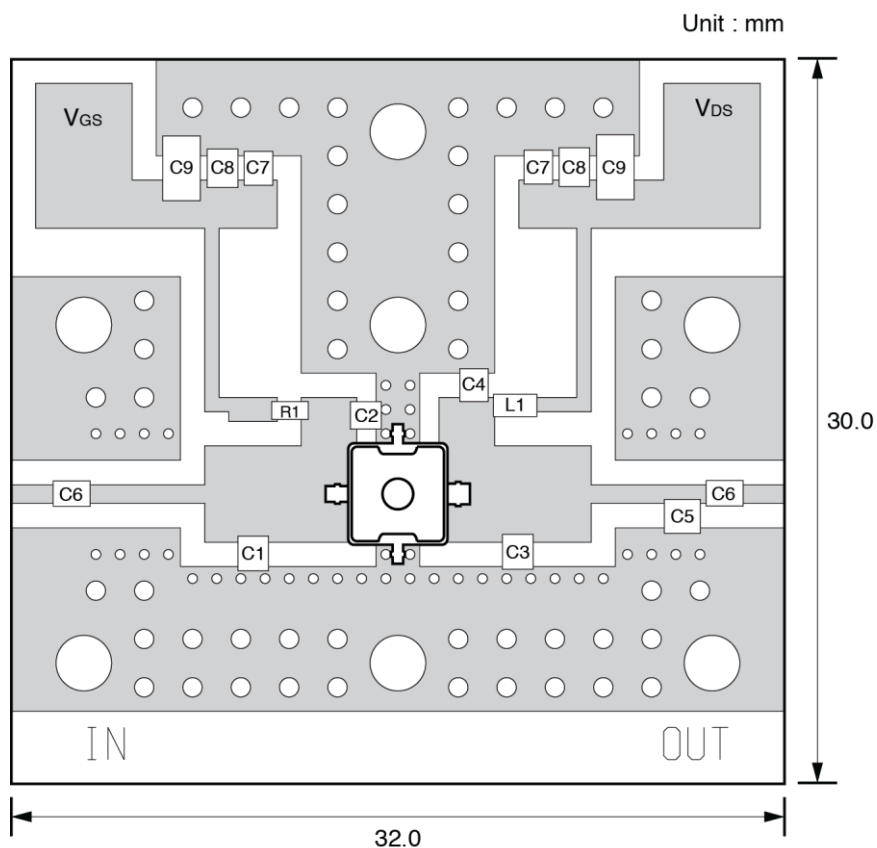
- S-parameters and noise parameters are provided on our Web site in a format (S2P) that enables the direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.
- Click here to download S-parameters.
- [RF and Microwave] ® [Device Parameters]
- URL <http://www.necel.com/microwave/en/>

LARGE SIGNAL IMPEDANCE ($V_{DS} = 3.0\text{ V}$, $I_D = 200\text{ mA}$, $f = 2.45\text{ GHz}$, $P_{out} = 400\text{ mW}$)

f (GHz)	$Z_{in} (\Omega)$	$Z_{OL} (\Omega)$ ^{Note}
2.45	2.96 -j7.78	3.36 -j8.42

Note Z_{OL} is the conjugate of optimum load impedance at given voltage, idling current, input power and frequency.

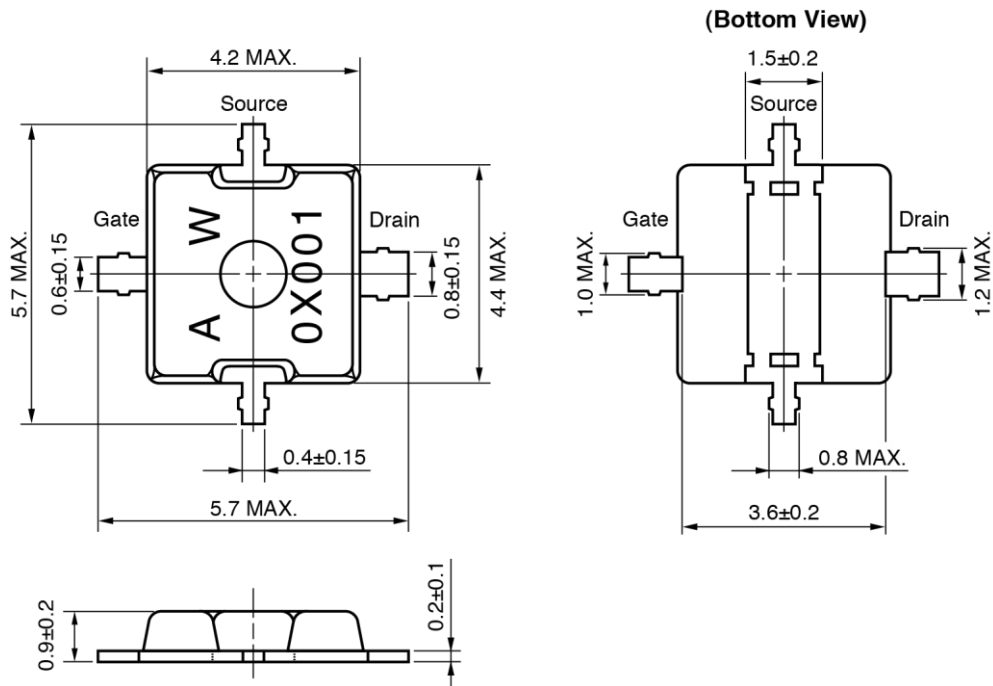
EVALUATION BOARD FOR 2.45 GHz



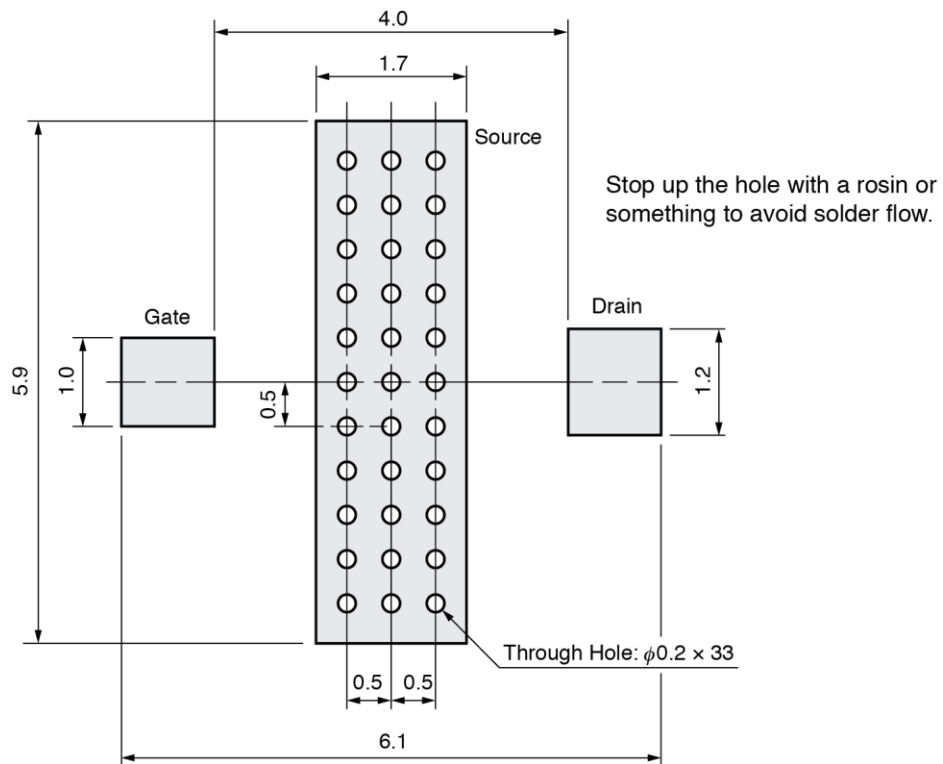
Symbol	Value	Comment
C1	2.0 pF	
C2	1.4 pF	
C3	2.2 pF	
C4	0.8 pF	
C5	0.5 pF	
C6	10 pF	
C7	1 000 pF	
C8	0.22 μ F	
C9	3.3 μ F - 16V	
R1	1 000 Ω	
L1	22 nH	
Circuit Board	t = 0.4 mm, ϵ r = 4.5	R4775

PACKAGE DIMENSIONS

79A (UNIT: mm)



79A PACKAGE RECOMMENDED P.C.B. LAYOUT (UNIT: mm)



RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions	Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) : 260°C or below Time at peak temperature : 10 seconds or less Time at temperature of 220°C or higher : 60 seconds or less Preheating time at 120 to 180°C : 120±30 seconds Maximum number of reflow processes : 3 times Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	IR260
VPS	Peak temperature (package surface temperature) : 215°C or below Time at temperature of 200°C or higher : 25 to 40 seconds Preheating time at 120 to 150°C : 30 to 60 seconds Maximum number of reflow processes : 3 times Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	VP215
Wave Soldering	Peak temperature (molten solder temperature) : 260°C or below Time at peak temperature : 10 seconds or less Preheating temperature (package surface temperature) : 120°C or below Maximum number of flow processes : 1 time Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	WS260
Partial Heating	Peak temperature (pin temperature) : 350°C or below Soldering time (per pin of device) : 3 seconds or less Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	HS350-P3

Caution Do not use different soldering methods together (except for partial heating).

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9